

PJS6415AE

20V P-Channel Enhancement Mode MOSFET – ESD Protected

Voltage	-20 V	Current	-4.9A
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Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-4.9A < 60m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-4.2A < 70m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-2.5V$, $I_D@-3.1A < 96m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- ESD Protected 2KV HBM
- Lead free in comply with EU RoHS 2011/65/EU directives.
- Green molding compound as per IEC61249 Std.

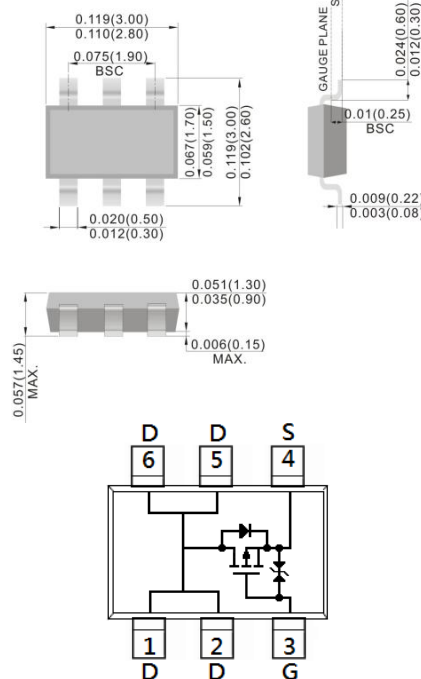
(Halogen Free)

Mechanical Data

- Case: SOT-23 6L-1 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams
- Marking: S5E

SOT-23 6L-1

Unit : inch(mm)



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-20	V
Gate-Source Voltage		V _{GS}	±12	V
Continuous Drain Current		I _D	-4.9	A
Pulsed Drain Current		I _{DM}	-19.6	A
Power Dissipation	T _a =25°C	P _D	2	W
	Derate above 25°C		16	mW/°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55~150	°C
Typical Thermal resistance		R _{θJA}	62.5	°C/W
- Junction to Ambient ^(Note 3)				



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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.5	-0.77	-1.2	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4.9A	-	50	60	mΩ
		V _{GS} =-4.5V, I _D =-4.2A	-	58	70	
		V _{GS} =-2.5V, I _D =-3.1A	-	80	96	
		V _{GS} =-1.8V, I _D =-0.5A	-	140	180	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	-	±6	±10	uA
Dynamic (Note 5)						
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-4.9A, V _{GS} =-4.5V (Note 1,2)	-	6.9	-	nC
Gate-Source Charge	Q _{gs}		-	1.5	-	
Gate-Drain Charge	Q _{gd}		-	1.9	-	
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, f=1.0MHZ	-	602	-	pF
Output Capacitance	C _{oss}		-	70	-	
Reverse Transfer Capacitance	C _{rss}		-	47	-	
Turn-On Delay Time	td _(on)	V _{DD} =-10V, I _D =-4.9A, V _{GS} =-4.5V, R _G =3Ω (Note 1,2)	-	8.8	-	ns
Turn-On Rise Time	tr		-	66	-	
Turn-Off Delay Time	td _(off)		-	29	-	
Turn-Off Fall Time	tf		-	14	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	-1.5	A
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V		-0.79	-1.0	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited
5. Guaranteed by design, not subject to production testing

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TYPICAL CHARACTERISTIC CURVES

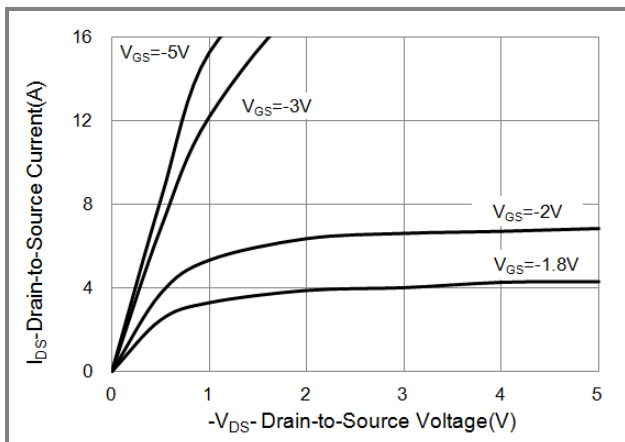


Fig.1 On-Region Characteristics

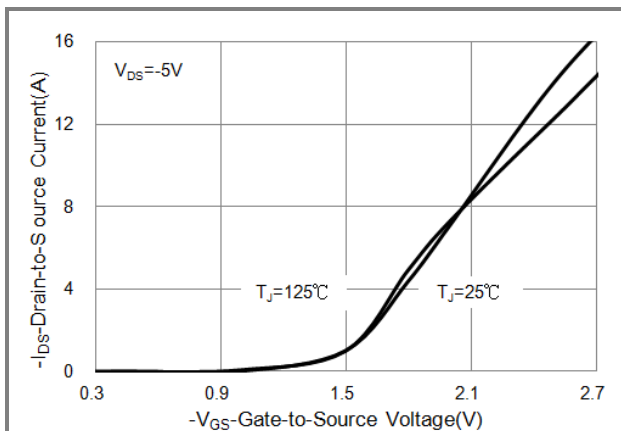


Fig.2 Transfer Characteristics

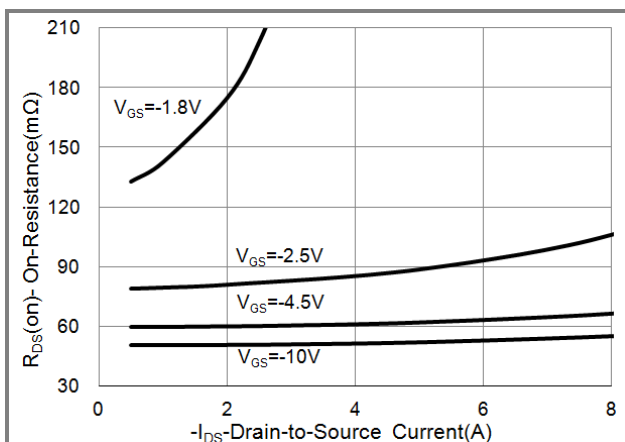


Fig.3 On-Resistance vs. Drain Current

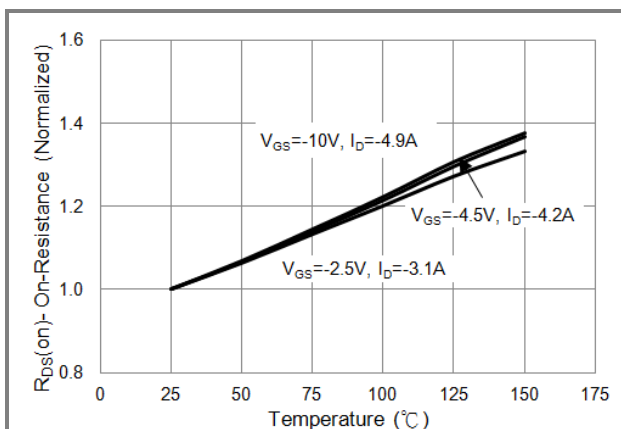


Fig.4 On-Resistance vs. Junction temperature

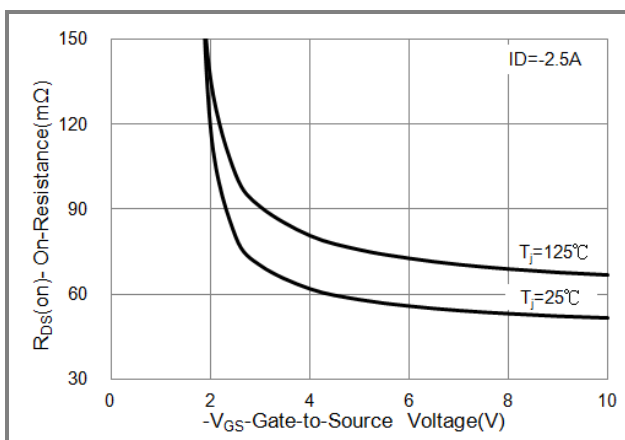


Fig.5 On-Resistance Variation with VGS.

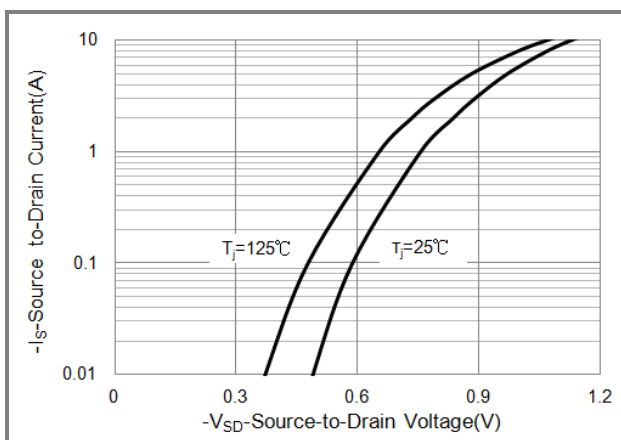


Fig.6 Body Diode Characteristics



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TYPICAL CHARACTERISTIC CURVES

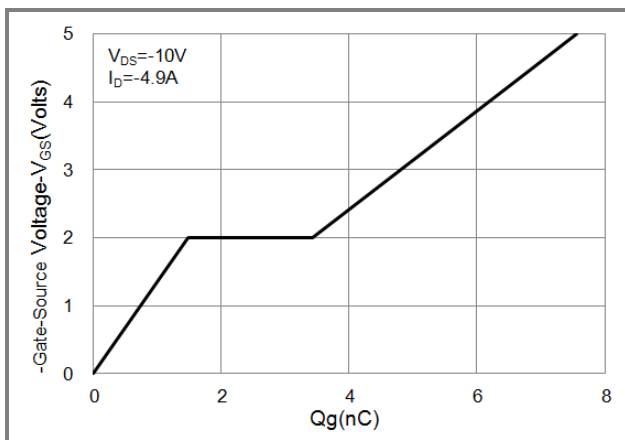


Fig.7 Gate-Charge Characteristics

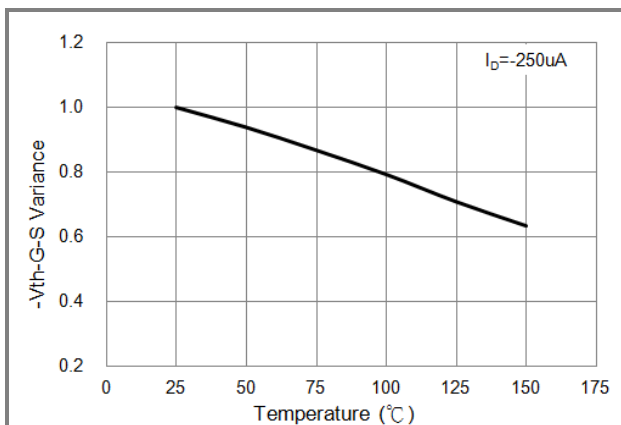


Fig.8 Threshold Voltage Variation with Temperature.

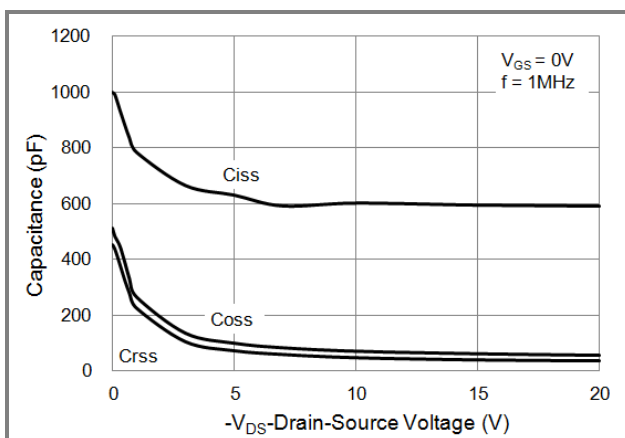


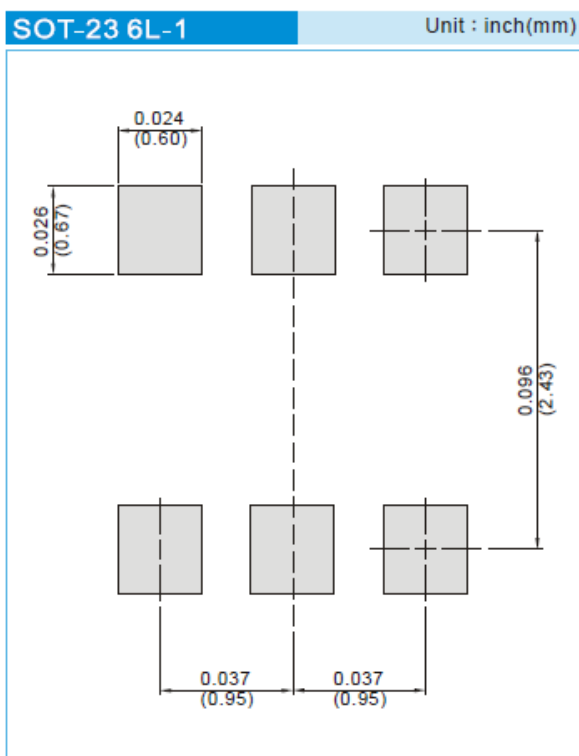
Fig.9 Capacitance vs. Drain-Source Voltage.

PJS6415AE

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6415AE_S1_00001	SOT-23 6L-1	3K pcs / 7" reel	S5E	Halogen free

MOUNTING PAD LAYOUT





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